

Printed Pages: 02

Sub Code: EEE403

Paper Id:

120406

Roll No.

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B. TECH.
(SEM IV) THEORY EXAMINATION 2017-18
ELECTRICAL & ELECTRONICS ENGINEERING MATERIALS

Time: 3 Hours

Total Marks: 100

Note: 1. Attempt all Sections. If require any missing data; then choose suitably.

SECTION A

1. Attempt all questions in brief. 2 x 10 = 20
- a. What do you mean by unit cell?
 - b. What is coordination number?
 - c. Explain space lattice.
 - d. Why Molybdenum is harder than Vanadium?
 - e. What are the general properties of conductor?
 - f. Explain resistivity and factor affecting resistivity of electrical materials
 - g. What are the characteristic of semiconductor materials?
 - h. What are the differences between intrinsic and extrinsic semiconductor?
 - i. What are magnetic domains?
 - j. What are the applications of magnetostriction?

SECTION B

2. Attempt any three of the following: 10 x 3 = 30
- a) List the various X-ray diffraction techniques and explain any two of them in detail.
 - b) Explain the properties and use of Copper, Aluminium and steel as conductor material.
 - c) What s PN junction diode? explain its working and characteristic.
 - d) Explain Hall Effect and its applications also derive the relation for determining the mobility using this effect.
 - e) What are ferrites? Explain their magnetic and electric characteristics.

SECTION C

3. Attempt any one part of the following: 10 x 1 = 10
- (a) Explain atomic packaging factor and calculate its value for simple cube and body centered cube.
 - (b) What do you mean by Miller indices? Explain the procedure of finding Miller indices and its important features.
4. Attempt any one part of the following: 10 x 1 = 10
- (a) A coil of copper wire has a resistance of 100 ohm at 25°C. Calculate its resistance at 60 °C. The temperature co-efficient of resistance is 0.00427 at 0°C.
 - (b) Explain (i) Photo electric effect (ii) Super conductivity in detail.
5. Attempt any one part of the following: 10 x 1 = 10
- (a) The mobility of silicon are $\mu_e = 0.147 \text{ m}^2/\text{V-s}$ and $\mu_h = 0.035 \text{ m}^2/\text{V-s}$ at room temperature. If the carrier density in the material is known to be $1.1 \times 10^{16} / \text{m}^3$, calculate the resistivity of silicon.

- (b) Explain the difference between doping and alloying. Also explain Thermister and Zener diode.

6. Attempt any one part of the following: 10 x 1 = 10

- (a) Classify the magnetic materials in detail.
(b) What do you mean by magnetic anisotropy? Explain the characteristics of soft magnetic materials.

7. Attempt any one part of the following: 10 x 1 = 10

- (a) Explain different types of losses in magnetic materials.
(b) Explain Meissner effect and relation for heat developed in current carrying conductor.